



MMBT4126

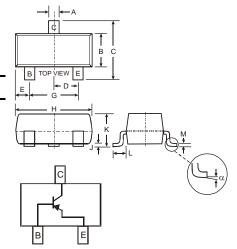
PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (MMBT4124)
- Ideal for Low Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking (See Page 3): K2B
- Ordering & Date Code Information: See Page 3
- Weight: 0.008 grams (approximate)



	SOT-23									
Dim	Min	Max								
Α	0.37	0.51								
В	1.20	1.40								
С	2.30	2.50								
D	0.89	1.03								
E	0.45	0.60								
G	1.78	2.05								
Н	2.80	3.00								
J	0.013	0.10								
K	0.903	1.10								
L	0.45	0.61								
М	0.085	0.180								
α	0°	8°								
All Dir	nensions	in mm								

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EBO}	-4.0	V
Collector Current - Continuous (Note 1)	I _C	-200	mA
Power Dissipation (Note 1)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-25	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}		_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-4.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	-50	nA	$V_{CB} = -20V, I_{E} = 0V$
Emitter Cutoff Current	I _{EBO}	_	-50	nA	$V_{EB} = -3.0V, I_{C} = 0V$
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h	120	360		$I_C = -2.0 \text{mA}, V_{CE} = -1.0 \text{V}$
DC Current Gain	h _{FE}	60	—		$I_C = -50 \text{mA}, V_{CE} = -1.0 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-0.40	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-0.95	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}		10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_C = 0$
Small Signal Current Gain	h _{fe}	120	480	_	$V_{CE} = 1.0V, I_{C} = -2.0mA,$ f = 1.0kHz
Current Gain-Bandwidth Product	f _T	250	_	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Noise Figure	NF	_	4.0	dB	$V_{CE} = -5.0V$, $I_{C} = -100\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead. Halogen and Antimony Free.
- 3. Short duration pulse test used to minimize self-heating effect.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.



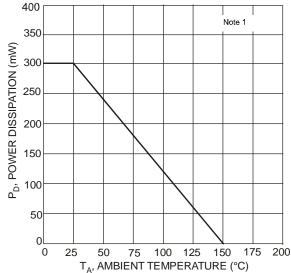


Fig. 1, Max Power Dissipation vs. Ambient Temperature

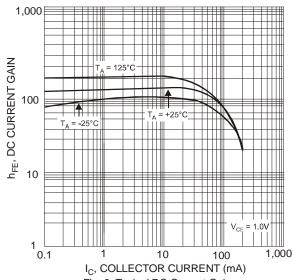


Fig. 3, Typical DC Current Gain vs. Collector Current

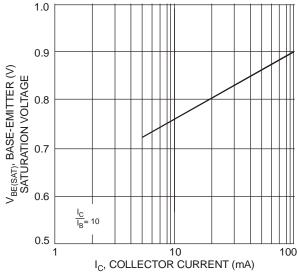


Fig. 5, Typical Base-Emitter
Saturation Voltage vs. Collector Current

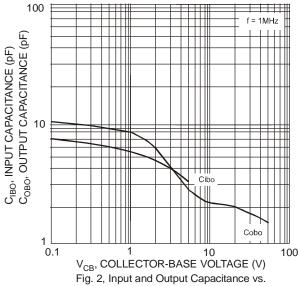


Fig. 2, Input and Output Capacitance vs.
Collector-Base Voltage

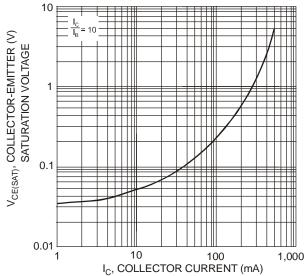


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

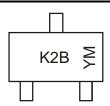


Ordering Information (Note 5)

Device	Packaging	Shipping
MMBT4126-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K2B = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Χ	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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